

What Is Claimed Is:

1. A metal-insulator-metal (MIM) capacitor process, comprising:
 - forming a first metal layer on a substrate, wherein a portion of the first metal layer is utilized as the lower plate of the MIM capacitor;
 - forming an etch stop layer on the substrate and the first metal layer, wherein a portion of an etch stop layer is utilized as the insulator for the MIM capacitor; and
 - forming a second metal layer on the substrate and portion of an etch stop layer, wherein a portion of the second metal layer is utilized as the upper plate of the MIM capacitor;

wherein the first and the second metal layers include copper or a copper alloy.
2. The process according to claim 1, wherein the stop layer includes a silicon nitride layer.
3. The process according to claim 1, wherein the second metal layer is polished by chemical-mechanical polishing.
4. The process according to claim 1, wherein the first metal layer is polished by chemical-mechanical polishing.